

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings of claims in the application:

**Listing of Claims:**

1-17. Canceled.

18. (Currently amended) A method for forming a semiconductor device, the method comprising:

- a) providing a semiconductor substrate having a first region of a first conductivity type;
- b) forming a second region of a second conductivity type in the semiconductor substrate such that the first and second regions form a p-n junction; and
- c) ~~forming a first charge control electrode; and~~
- d) forming a first and second charge control electrodes adjacent to but insulated from one of the first and second regions, along a dimension parallel to flow of current through the semiconductor device, wherein the first charge control electrode is adapted to be biased differently than the second ~~first~~ charge control electrode.

19. (currently amended) A method for forming a semiconductor device, the method comprising: ~~The method of claim 18 further comprising~~

providing a semiconductor substrate having a first region of a first conductivity type;

forming a second region of a second conductivity type in the semiconductor substrate;

~~forming a trench in the semiconductor substrate and wherein;~~

~~forming the a first charge control electrode in the trench by comprises depositing a conductive material in the trench and then etching the deposited conductive material; and~~

forming a second charge control electrode in the trench by depositing a conductive material in the trench and then etching the deposited conductive material, wherein the

first charge control electrode is adapted to be biased differently than the second charge control electrode.

20. Canceled.

21. (Original) The method of claim 18 further comprising:  
forming a trenched gate structure in the semiconductor substrate.

22. (Original) The method of claim 18 wherein the first and second charge control electrodes comprise polysilicon.

23. (Original) The method of claim 18 wherein the method further comprises forming a plurality of biasing elements on or in the semiconductor substrate, wherein the biasing elements are adapted to bias the first and second charge control electrodes at different voltages.

24. (Original) The method of claim 18 wherein the semiconductor device is a power MOSFET.

25-29. Canceled.

30. (Original) A method for forming a field effect transistor comprising:

a) providing a semiconductor substrate of a first conductivity type having a major surface, a drift region, and a drain region;

b) forming a well region of a second conductivity type in the semiconductor substrate;

c) forming a source region of the first conductivity type in the well region;

d) forming a source contact layer on the source region;

e) forming a gate electrode adjacent to the source region;

f) forming a charge control electrode in the drift region, wherein the charge control electrode is adapted to be biased at a different potential than the gate electrode or the source contact layer, and is adapted to control the electric field in the drift region; and

g) forming a dielectric material around the charge control electrode.

31. (Original) The method of claim 30 wherein the gate electrode is a  
trenched gate electrode.

32. (Original) The method of claim 30 further comprising:  
forming a biasing element, wherein the biasing element is adapted to bias the  
charge control electrode.